

SILICON NPN RF POWER TRANSISTOR

DESCRIPTION:

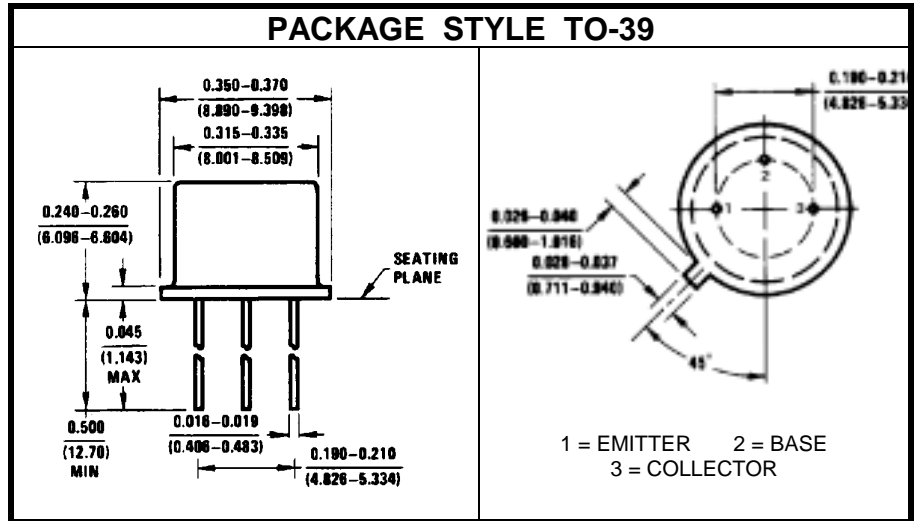
The **ASI SD1127** is designed for VHF mobil communications applications up to 175 MHz.

FEATURES:

- Grounded Emitter The **ASI SD1127**
- Gp 12 dB @ 12.5V 175 MHz
- P_{out} 4.0 V Min.

MAXIMUM RATINGS

I _C	0.64A
V _{CB}	36 V
V _{CE}	18 V
P _{DISS}	8 W @ T _C = 25 °C
T _J	-65 °C to +200 °C
T _{STG}	-65 °C to +200 °C
θ _{JC}	21.9 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV _{CEO}	I _C = 10 mA		18			V
BV _{CES}	I _C = 5 mA		36			V
BV _{EBO}	I _C = 1.0 mA		4.0			V
I _{CBO}	V _{CE} = 15 V				.25	mA
H _{FE}	V _{CE} = 5.0 V	I _C = 50 mA	10		100	---
C _{OB}	V _{CE} = 15 V	f = 1.0 MHz			20	pf
G _{PE}	V _{CE} = 12.5 V	f = 175 MHz	12			dB
η	V _{CE} = 12.5 V	P _{PUT} = 4.0 W				
IMPEDANCE	V _{CC} = 12.6 V	P _{IN} = 0.2 W	f = 136 MHz	Z _{IN} = 3.0 - j3.8	Z _{CL} = 12.8 - j11	Ω
	V _{CC} = 12.6 V	P _{IN} = 0.2 W	f = 155 MHz	Z _{IN} = 4.0 - j2.0	Z _{CL} = 11 - j14.8	
	V _{CC} = 12.6 V	P _{IN} = 0.2 W	f = 175 MHz	Z _{IN} = 4.3 - j5.8	Z _{CL} = 13 - j20	